



Impact of Fin Dimensions on Performance of Adder and Subtractor

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ABSTRACT: The FinFET architecture has emerged a viable contender for the ultimate scalability of CMOS devices. FinFET structure offers better control over device leakage currents than the conventional bulk MOSFET structure. In this work the adder and subtractor implementation using 30 nm technology. The figure of merit measure for adder and subtractor are power and delay. Based on the simulation results, it is found that the fin thickness (T_{fin}), fin height (H_{fin}) are very important deciding factor for power and delay. There is a phenomenal increase in short channel effects when the fin dimensions are increased. From the simulation average power is calculated for the variation in H_{fin} for full adder and full subtractor to 34% and 24 % when the height of fin is minimum while in case when height is maximum the average power of full adder and full subtractor is increased to 51% and 26% respectively. On the other hand power increases 14% and 16% when T_{fin} is maximum for full adder and subtractor respectively. And when T_{fin} is minimum power reduces to 21% and 24% respectively. Delay calculation for different values of H_{fin} for full adder and full subtractor is 17 % and 16% increase in delay when H_{fin} is minimum.while for maximum value of H_{fin} delay is reduced to 58% and 27% respectively. Similarly delay for full adder and full subtractor is 13% and 10% increase when T_{fin} is minimum and for maximum values of T_{fin} delay reduces to 10% and 15% respectively.

KEYWORDS: *FinFET, Adder, Subtractor, circuit design, device simulation, Hspice, Parameter variation.*

I. INTRODUCTION

The emergence of novel CMOS devices structures as alternative to conventional bulk MOSFET is one reason for the continued trend in scaling of MOS devices. The quasi-planer FinFET is one such candidate to replace bulk CMOS device due to its superior control over the short channel effects, lower leakage currents and immunity towards the random dopant fluctuation effects [1]-[2]. The working principle is same as that of planer MOSFET. The conventional bulk MOSFETs suffer from short channel effects at lower technology nodes due to the fact that as the source and drain regions are brought closer together, the drain region is better able to control the carriers in the channel than the gate. In order to counter this, thinner gate tunnelling leakage current in the device [3]. The FinFET structure has its channel formed perpendicular to the substrate and the channel width can be increased by either increasing the fin height or by number of fins between the source and drain. Increasing the gate area to improve the drive current is not beneficial as the gate capacitance is also increased [4]. At the same time increased drive current is useful when driving interconnect dominated systems such as memories. Addition and subtraction are most commonly used arithmetic operation in arithmetic and Logic Unit (ALU). Back gate is used to control the threshold voltage (V_{th}) of the front gate, which is very important parameter of the device [5]. This helps in optimizing the circuits in terms of delay, and power. The thickness of the fin determine the effective channel length of the device. The basic finFET structure shown in figure 1 below.

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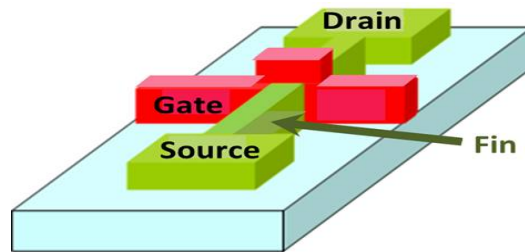


Figure 1: Basic structure of finFET

The wrap around structure provide a better electrical control over the channel and thus help to reducing the leakage current and overcoming short channel effect. In the finFET the silicon body has been rotated on its edge into a vertical orientation so only source and drain regions are placed horizontally about the body as in a conventional planner FET. The saperate biasing in dual gate device easily provide multiple threshold voltages. A gate can also be fabricated at the top of the fin, in which case it is triple gate FET, The width of the finFET is quantised due to a vertical gate structure. The fin height determine the minimum transistor width(W_{min}) with the two gate of the single FET tied together, W_{min} is

$$W_{min} = 2 * H_{fin} + T_{fin}$$

Where H_{fin} - height of the fin, T_{fin} - thickness of the si body. FinFET are designed to use multiple fin to achieve larger channel width[4]. Source/drain pads connect the fin in parallel as the no. of fins is increased, the current through the device increases For high layout density, the ratio between fin height and the achievable pitch between to successive fins has to be maximized[5]. In particular the fin height has to be higher than the pitch between the fingers in order to obtained the same drive current per silicon area as per planar double gate transistors to improve the ratio with respect to the pitch achievable by lithography, the use of spacer or hard mask for the fin patterning can be use that way the fin density can be doubled[13]. FinFET offers distinct advantages for scaling to very short gate lengths[7]-[8]. Fabrication of the FinFET is similar to conventional CMOS process, with only minor disruptions, offering the potential for a rapid deployment to manufacturing. The channel of the FinFET is a tiny chunk of undoped silicon perpendicular to the substrate[9]. The control of short channel effects for FinFETs is provided by the two gates without aggressively scaling down the gate-oxide thickness and increasing the channel doping density. Also the finFET come in many varients like shorted gate(SG) mode, Independent gate(IG) mode, low power (LP) mode and hybrid mode (IG/LP). In shorted gate(SG) mode of operation, the two gates are biased together to turn on the device, providing maximum gate drive. In the Independent gate(IG) mode of operation, the two gates are electrically independent[9]. In Low power(LP) mode of operation the back gate is tied to a reverse-bias voltage to reduce leakage power. In hybrid mode of operation IG and LP modes are combined[11].

II. DESIGN OF FULL ADDER AND SUBTRACTOR

Full Adder

A full adder is a combinational circuit that forms the arithmetic sum of three input bits. It consists of three inputs and two outputs. In this design, the designated three inputs are A, B and C_{in} . The third input C_{in} represents carry input to the first stage. The output are SUM and CARRY. The Boolean expression for SUM and CARRY bits are given below.

$$\begin{aligned} \text{SUM} &= A \text{ xor } B \text{ xor } C \\ \text{CARRY} &= AB + BC_{in} + C_{in}A \end{aligned}$$

Sum bit is EXOR function of all three Inputs and carry bit is AND function of three inputs. The transistor level diagram of full adder is shown in Figure 2.

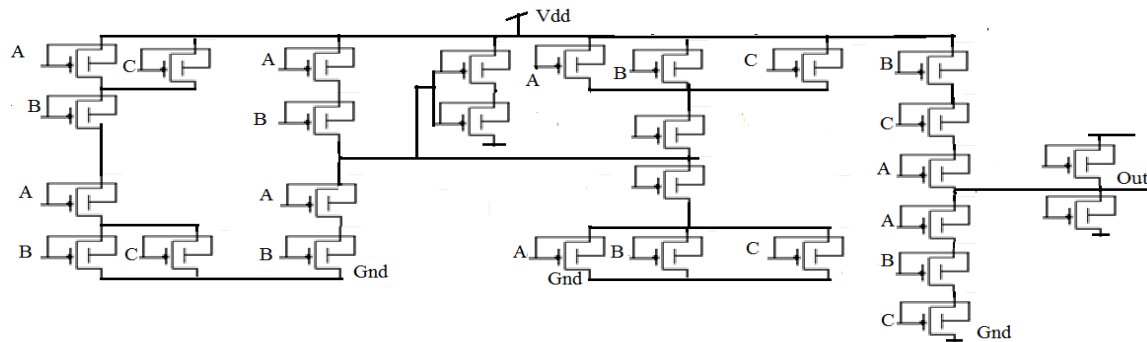


Figure 2. Transistor level diagram of full adder

Full Subtractor

A full subtractor is a combinational circuit that performs a subtraction between two binary bits and ‘1’ may have been borrowed by a lower significant stage. This circuit has three inputs and two outputs. In this design the designated three inputs are A,B and Bin. The third input Bin represent the borrow input to the first stage. The outputs are DIFF and Bout. The Boolean expression for DIFF and Bout bits are given below.

$$\text{DIFF} = A \oplus B \oplus \text{Bin}$$

$$\text{Bout} = AB + A\text{Bin} + B\text{Bin}$$

The transistor level diagram of full subtractor is shown below in Figure 3.

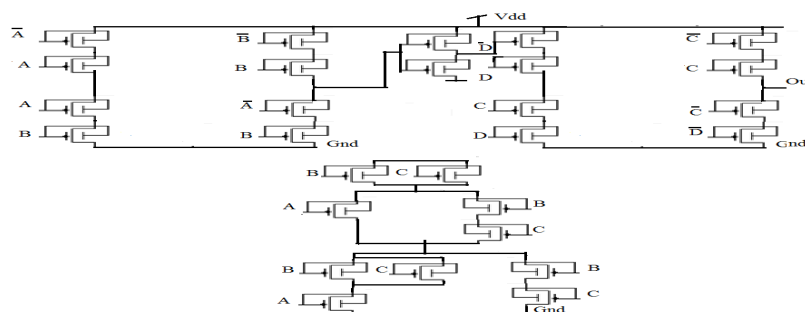


Figure 3. Transistor level diagram of full subtractor

Variation in Dimensions of FinFET

The parameters considered here are height of fins (Hfin), thickness of fins (Tfin). These parameters are varied over a range of values to capture their effect on average power and delay. Here in Table 1 show the values of the parameters for 30nm are.

Table 1. FinFET device parameters and their variations

Parameter	Value	Variation
Thickness of fin (Tfin) (nm)	15	5 – 20
Height of fin (Hfin) (nm)	30	20 – 40

The Hfin is varied for some range of values when Hfine is reduced it also impact on device channel length which also decreases with Hfin. So the current drive through the gate is also reduced but the delay of device is increase due to lower current drive through the gate. The fin thickness is varied from 5nm – 20nm and measure the power and delay.

III. RESULTS AND DISSCUSION

The Input and output waveform of 1-bit adder are shown below in Figure 4 .According to the input signal provided as A B and Cin the outputs sum and CARRY were properly generated verified with truth-table of full adder..

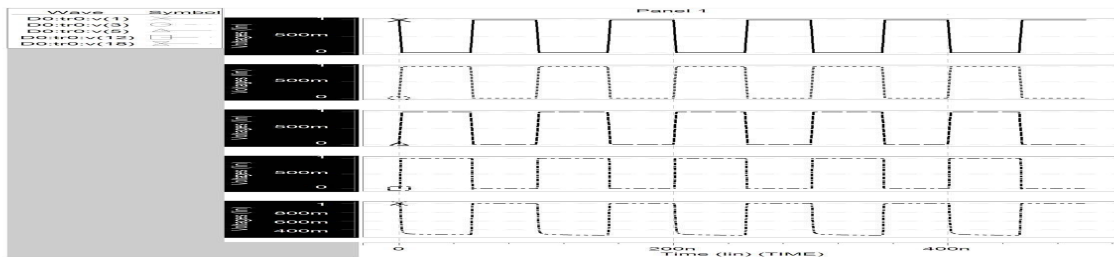


Figure 4. Transient analysis of full adder

Transient response of input and output oo 1-bit subtractor is shown below in Figure 5 where A,B and C are the inputs and diff., bout are outputs.

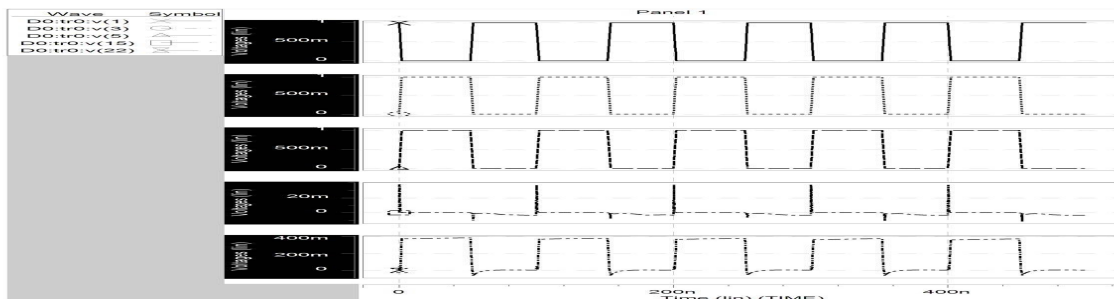


Figure 5. Transient analysis of full subtractor.

Effect of Fin Height on Delay and power

Here the fin height (Hfin) is varied as 20nm, 25nm, 30nm, 35nm, 40nm. As fin height decrease, leakage current decreases because of increase in its parasitic resistance (Rp). So that the reduction in power leakage and delay should be increased as the height of the fin decreases, while on the other hand when Hfin increased the current drive also increase due to increase in the gate area so the delay reduced but it also increase the gate leakage resulting the increase in power dissipation. Table 2 below shows the variation in average power at different value of Hfin.

Table 2. Variation in average power for full adder and full subtractor

Fin Height	20nm	25nm	30nm	35nm	40nm
Full subtractor	0.85pw	1,07pw	0.097nw	0.149nw	1.719nw
Full adder	0.55pw	2.18pw	0.041nw	0.519nw	1.62nw

Figure 6.a) Show the graphical representation of average power for full adder and b) shows the graphical representation of average power for full subtractor.

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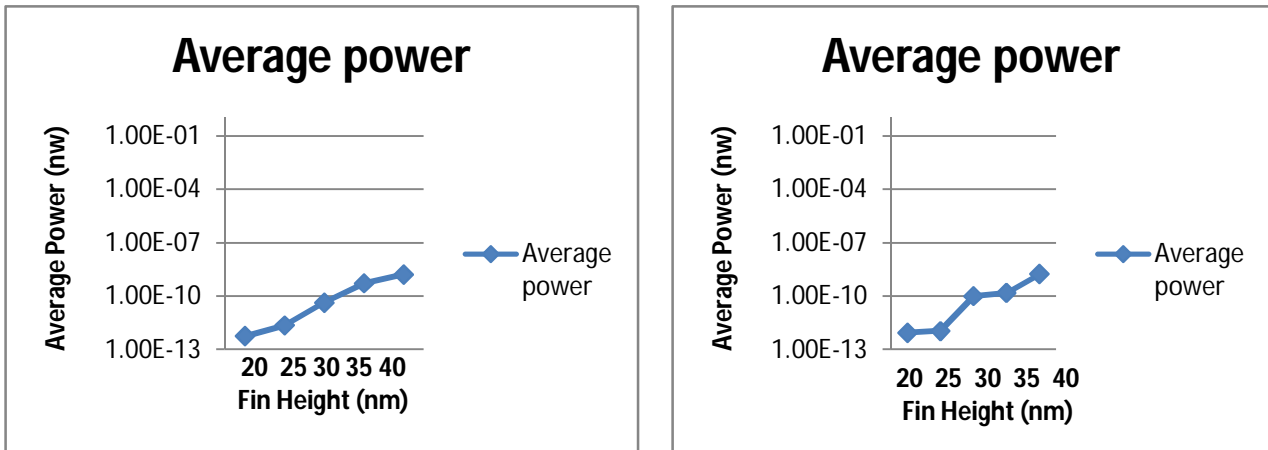


Figure 6. The effect of Fin Height on a) Average power of full adder b) Average power of full subtractor

As the height of the fin increases it will impact on delay started to reduce because of the increase in drive current through the gate. Table 3 show the variation in delay at different values for Hfin.

Table 3 Variation in Delay for different values of Hfin

Fin Height	20nm	25nm	30nm	35nm	40nm
Full adder	54.2ns	46.2ns	39.1ns	23.6ns	16.2ns
Full subtractor	69.23ns	62.4ns	59.1ns	49.4ns	43.4ns

The effect of Fin height on delay is shown in Figure 7 below a) for full adder and b) for full subtractor. It show that as the value of Hfin is increases the delay started to reduce while is the Hfin is reduces it also increase the delay.

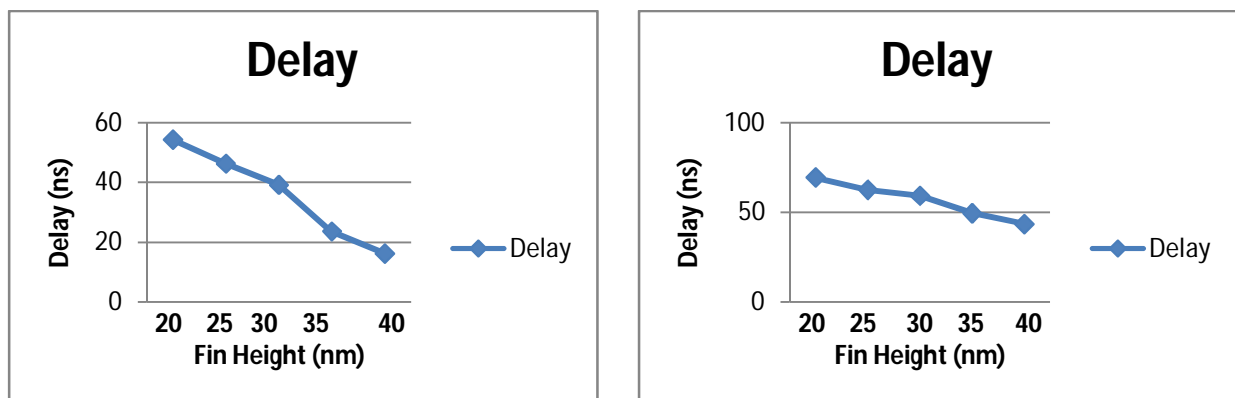


Figure 7. Effect of Fin Height on a) Delay of full adder b) Delay of full subtractor.

Effect of Thickness of Fin on Delay and Power

The thickness of Fin is varied as 5nm, 10nm, 15nm, 20nm. Leakage current increases with increase in fin width due to reduced control of the gate over the channel because the leakage current occurs at the middle of the fin, which is the more remote area from the gate. But as fin width decreases, the middle part of the fin has more control from the gate, so the leakage current decreases. Table 4 below show the variation in average power for different values of Tfin.

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Table 4. Variation in average power for different values of Tfin

Thickness of fin	20nm	15nm	10nm	5nm
Full subtractor	0.144nw	0.0337nw	0.0127nw	2.64pw
Full adder	0.115nw	0.0419nw	5.12pw	1.43pw

The graph in Figure 8 shows that as Tfin is increased the due to increase in leakage power also increases while as the reduces the Tfin the power stated to decrease .

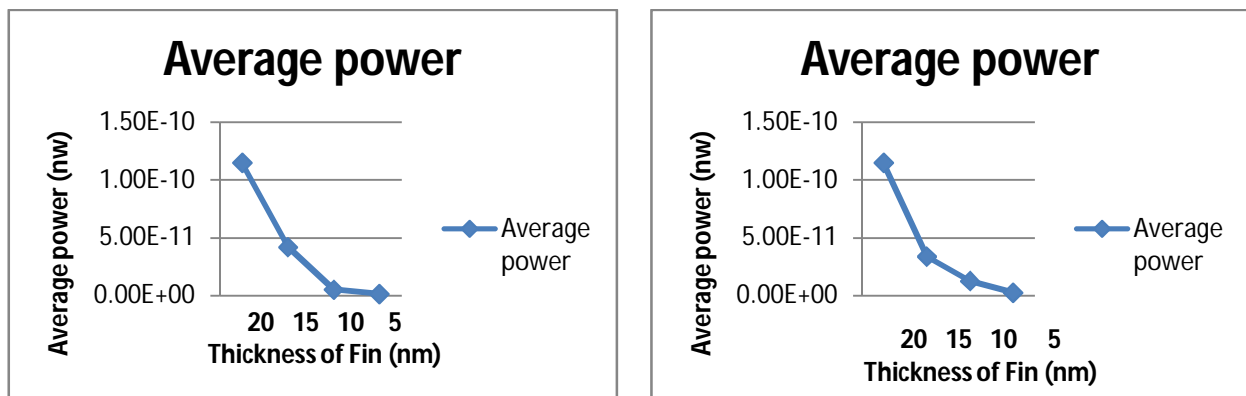


Figure 8. Effect of Thickness of Fin on a) average power of full adder b) average power of full subtractor.

The effect of thickness of fin on the delay of full adder is shown below in Table 5 which shows that as the thickness of the fin is increases delay started to decrease while decreasing the value of Tfin delay is increasing due to more current drive through the channel delay is decreased while as the Tfin decreases it reduces the current drive resulting increase in delay. Similarly for full subtractor.

Table 5. Variation in average power for different values of Tfin

Thickness of fin	20nm	15nm	10nm	5nm
Full adder	34.62ns	39.2ns	41.6ns	43.3ns
Full subtractor	53.1ns	59.1ns	61.34ns	62.1ns

The graphical representation for the different values of Tfin for delay when Tfin is at maximum value the delays at minimum value but as the value of Tfin is reduces it changes the value of delay and it stated to increases as the Tfin reduces. Figure 9 below shows variations for full adder and subtractor respectively.

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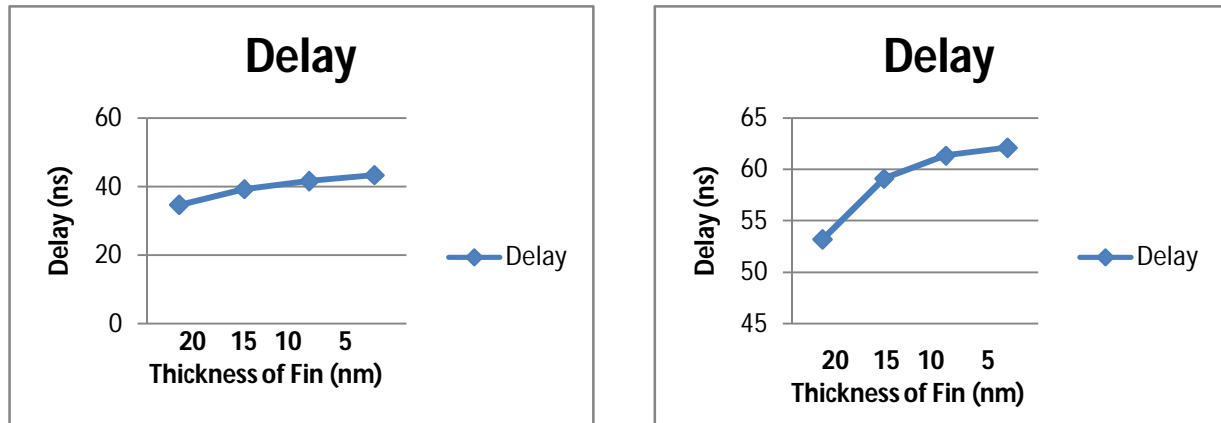


Figure 9. a) Effect of Thickness of Fin on a) Delay of full adder b) Delay of full subtractor.

IV. CONCLUSION

The design of the Full adder and full subtractor has been designed by using finFET. The design is performed in 30nm technology. The effect of the dimensions of the FinFET on 1-bit full adder and 1-bit full subtractor is shown. The delay and power is calculated for different values of Hfin and Tfin. Which shows that change in the dimensions of the device can also affect the performance of the device the power is calculated for the variation in Hfin for full adder and full subtractor when fin height is minimum the power is reduced to 34% and 24% while in case when height is maximum the average power of full adder and full subtractor is increased to 51% and 26% respectively. On the other hand when Tfin is varied the change in average power for full adder and full subtractor when Tfin is maximum power increased 14% and 16% and when Tfin is minimum power reduces to 21% and 24% respectively. Delay calculation for different values of Hfin for full adder and full subtractor when hfin is minimum is 17% and 16% increase in delay, while for maximum value of Hfin delay is 58% and 27% respectively. And change in delay for full adder and full subtractor when Tfin is minimum is 13% and 10% and for maximum values of Tfin is 10% and 15% respectively.

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BIOGRAPHY



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